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GP1S093HCZ0F

Gap: 2mm Slit: 0.3mm Phototransistor Output, **Compact Transmissive Photointerrupter**



Description

GP1S093HCZ0F is a compact-package, phototransistor output, transmissive photointerrupter, with opposing emitter and detector in a molding that provides non-contact sensing. The compact package series is a result of unique technology combing transfer and injection molding.

The device has a low profile, and wide gap.

Features

- 1. Transmissive with phototransistor output
- 2. Highlights :
 - Compact Size
- 3. Key Parameters :
 - · Gap Width : 2mm
 - Slit Width (detector side): 0.3mm
- Package : 4.5×2.6×2.9mm
- 4. RoHS directive compliant

■ Agency approvals/Compliance

1. Compliant with RoHS directive

Applications

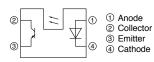
- 1. General purpose detection of object presence or motion.
- 2. Example : printer, lens control for camera

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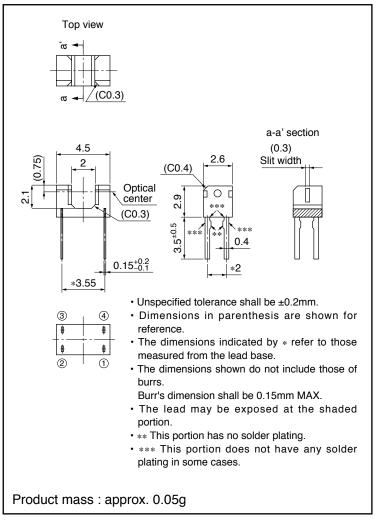
Internal Connection Diagram

Top view



■ Outline Dimensions

(Unit : mm)

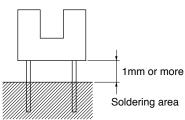


Plating material : SnCu (Cu : TYP. 2%)

Country of origin Japan



Abs	Absolute Maximum Ratings			$(T_a=25^{\circ}C)$
	Parameter	Symbol	Rating	Unit
	Forward current	I _F	50	mA
Input	Reverse voltage	V _R	6	V
	Power dissipation	Р	75	mW
	Collector-emitter voltage	V _{CEO}	35	V
Outout	Emitter-collector voltage	V _{ECO}	6	V
Output	Collector current	I _C	20	mA
	Collector power dissipation	P _C	75	mW
Total power dissipation		P _{tot}	100	mW
Operating temperature		T _{opr}	-25 to +85	°C
Storage temperature		T _{stg}	-40 to +100	°C
*1Soldering temperature		T _{sol}	260	°C



*1 For 5s or less

■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

•						u /	
Parameter			Condition	MIN.	TYP.	MAX.	Unit
Forward voltage		$V_{\rm F}$	I _F =20mA	-	1.2	1.4	V
Reverse current		I _R	V _R =3V	-	_	10	μΑ
Collector dark current		I _{CEO}	$V_{CE}=20V$	-	_	100	nA
Collector current		I _C	$V_{CE}=5V, I_{F}=5mA$	100	-	400	μΑ
Collector-emitter saturation voltage		V _{CE(sat)}	$I_F=10mA$, $I_C=40\mu A$	-	_	0.4	V
Response time	Rise time	t _r	V_{CE} =5V, I_C =100 μ A, R_L =1 $k\Omega$	_	50	150	μs
	Fall time	t _f		_	50	150	μs
	Forward voltage Reverse current Collector dark current Collector current Collector-emitter saturation	Forward voltage Reverse current Collector dark current Collector current Collector-emitter saturation voltage Response time	$\begin{tabular}{ c c c c } \hline Forward voltage & V_F \\ \hline Reverse current & I_R \\ \hline Collector dark current & I_{CEO} \\ \hline Collector current & I_C \\ \hline Collector-emitter saturation voltage & V_{CE(sat)} \\ \hline Response time & \hline Rise time & t_r \\ \hline \end{tabular}$	Forward voltage V_F $I_F=20mA$ Reverse current I_R $V_R=3V$ Collector dark current I_{CEO} $V_{CE}=20V$ Collector current I_C $V_{CE}=5V, I_F=5mA$ Collector-emitter saturation voltage $V_{CE(sat)}$ $I_F=10mA, I_C=40\mu A$ Response time Rise time t_r $V_{CE}=5V, I_C=100\mu A, R_I=1kQ$	Forward voltage V_F $I_F=20mA$ -Reverse current I_R $V_R=3V$ -Collector dark current I_{CEO} $V_{CE}=20V$ -Collector current I_C $V_{CE}=5V, I_F=5mA$ 100Collector-emitter saturation voltage $V_{CE(sat)}$ $I_F=10mA, I_C=40\muA$ -Response timeRise time t_r $V_{CE}=5V, I_C=100uA, R_I=1kQ$ -	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $





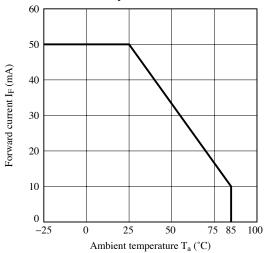
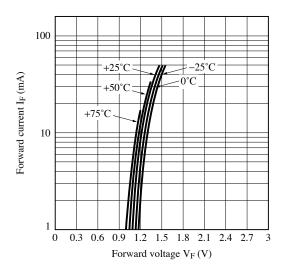


Fig.3 Forward Current vs. Forward Voltage





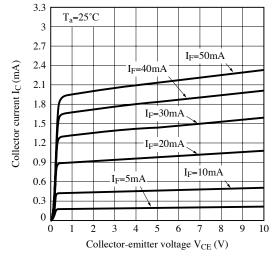
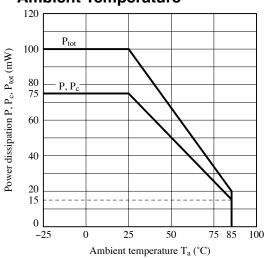
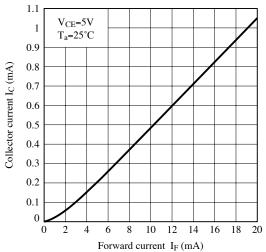


Fig.2 Power Dissipation vs. Ambient Temperature









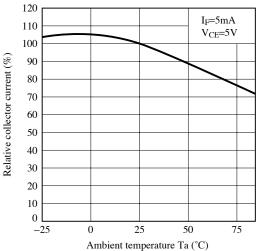




Fig.7 Collector-emitter Saturation Voltage vs. Ambient Temperature

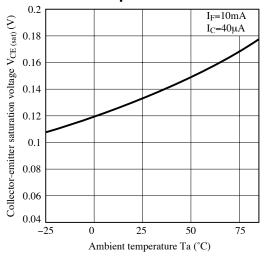


Fig.9 Response Time vs. Load Resistance

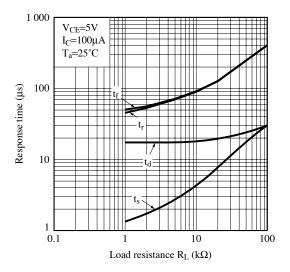


Fig.11 Detecting Position Characteristics (1)

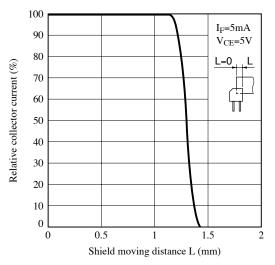


Fig.8 Collector Dark Current vs. Ambient Temperature

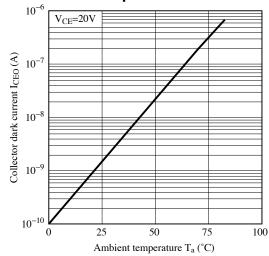


Fig.10 Test Circuit for Response Time

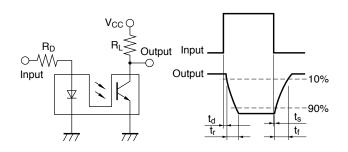
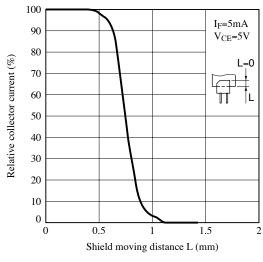


Fig.12 Detecting Position Characteristics (2)



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.



Design Considerations

• Design guide

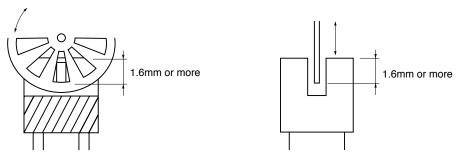
1) Prevention of faulty operation

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

2) Position of opaque board

Opaque board shall be installed at place 1.6mm or more from the top of elements.





This product is not designed against irradiation and incorporates non-coherent IRED.

Degradation

In general, the emission of the IRED used in photointerrupter will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

Parts

This product is assembled using the below parts.

• Photodetector (qty. : 1)

Category	Material	Maximum Sensitivity wavelength (nm)	Sensitivity wavelength (nm)	Response time (µs)	
Phototransistor	Silicon (Si)	930	700 to 1 200	20	

• Photo emitter (qty. : 1)

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3

Material

Case	Lead frame	Lead frame plating		
Black polyphernylene sulfide resin (UL94 V-0)	42Alloy	SnCu plating		



Manufacturing Guidelines

Soldering Method

Flow Soldering:

Soldering should be completed below 260°C and within 5 s.

Please solder within one time.

Soldering area is 1mm or more away from the bottom of housing.

Please take care not to let any external force exert on lead pins.

Please don't do soldering with preheating, and please don't do soldering by reflow.

Hand soldering

Hand soldering should be completed within 3 s when the point of solder iron is below 350°C. Please solder within one time.

Please don't touch the terminals directly by soldering iron.

Soldered product shall treat at room temperature.

Other notice

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the cooling and soldering conditions.

• Cleaning instructions

Solvent cleaning :

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

Ultrasonic cleaning :

Do not execute ultrasonic cleaning.

Recommended solvent materials :

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

Presence of ODC

This product shall not contain the following materials. And they are not used in the production process for this product. Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).
Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).



Package specification

Sleeve package

Package materials Sleeve : Polystyrene Stopper : Styrene-Elastomer

Package method

MAX. 100 pcs. of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

MAX. 50 sleeves in one case.

SHARP

Important Notices

• The circuit application examples in this publication are provided to explain representative applications of SHARP devices and are not intended to guarantee any circuit design or license any intellectual property rights. SHARP takes no responsibility for any problems related to any intellectual property right of a third party resulting from the use of SHARP's devices.

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(i) The devices in this publication are designed for use in general electronic equipment designs such as:

- --- Personal computers
- --- Office automation equipment
- --- Telecommunication equipment [terminal]
- --- Test and measurement equipment
- --- Industrial control
- --- Audio visual equipment
- --- Consumer electronics

(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection with equipment that requires higher reliability such as:

- --- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- --- Traffic signals
- --- Gas leakage sensor breakers
- --- Alarm equipment
- --- Various safety devices, etc.

(iii) SHARP devices shall not be used for or in connection with equipment that requires an extremely high level of reliability and safety such as:

- --- Space applications
- --- Telecommunication equipment [trunk lines]
- --- Nuclear power control equipment
- --- Medical and other life support equipment (e.g., scuba).

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